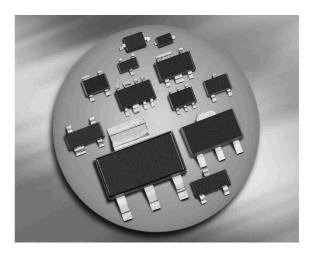


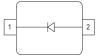
## Silicon Variable Capacitance Diode

- For VHF tuned circuit applications
- High figure of merit
- Pb-free (RoHS compliant) package





#### BB439



Туре	Package	Configuration	L <sub>S</sub> (nH)	Marking
BB439	SOD323	single	1.8	white 2

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V <sub>R</sub>	28	V	
Peak reverse voltage	V <sub>RM</sub>	30		
( $R \ge 5 \mathrm{k} \Omega$ )				
Forward current	I <sub>F</sub>	20	mA	
Operating temperature range	T <sub>op</sub>	-55 125	°C	
Storage temperature	T <sub>stg</sub>	-55 150		



Parameter	Symbol		Values		
		min.	typ.	max.	1
DC Characteristics					
Reverse current	I <sub>R</sub>				nA
V <sub>R</sub> = 28 V		-	-	20	
<i>V</i> <sub>R</sub> = 28 V, <i>T</i> <sub>A</sub> = 85 °C		-	-	200	
AC Characteristics					
Diode capacitance	CT				pF
V <sub>R</sub> = 1 V, <i>f</i> = 1 MHz		-	43	-	
<i>V</i> <sub>R</sub> = 2 V, <i>f</i> = 1 MHz		31.5	34.5	37.5	
<i>V</i> <sub>R</sub> = 3 V, <i>f</i> = 1 MHz		26.5	29	31.5	
V <sub>R</sub> = 25 V, <i>f</i> = 1 MHz		4.3	5.1	6	
Capacitance ratio	C <sub>T2</sub> /C <sub>T25</sub>	6	6.9	8	]
$V_{\rm R}$ = 2 V, $V_{\rm R}$ = 25 V, $f$ = 1 MHz					
Capacitance ratio	C <sub>T3</sub> /C <sub>T25</sub>	5	5.8	6.5	
$V_{\rm R}$ = 3 V, $V_{\rm R}$ = 25 V, $f$ = 1 MHz					
Capacitance matching <sup>1)</sup>	$\Delta C_{T}/C_{T}$	-	-	3	%
$V_{\rm R}$ = 3 V, $V_{\rm R}$ = 25 V, $f$ = 1 MHz					
Series resistance	r <sub>S</sub>	-	0.35	0.5	Ω
V <sub>R</sub> = 10 V, <i>f</i> = 100 MHz					
Figure of merit	Q				
V <sub>R</sub> = 3 V, <i>f</i> = 50 MHz		-	280	-	
<i>V</i> <sub>R</sub> = 25 V, <i>f</i> = 200 MHz		-	600	-	

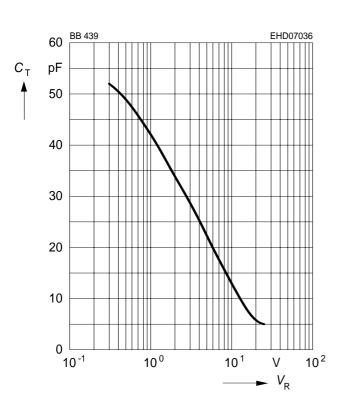
## **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

<sup>1</sup>For details please refer to Application Note 047.



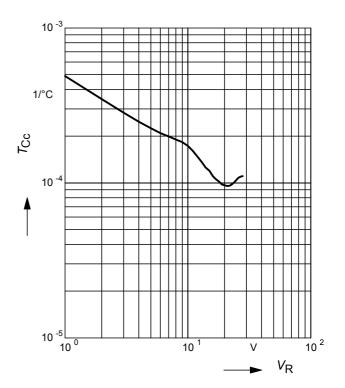
**Diode capacitance**  $C_{T} = f(V_{R})$ 

f = 1 MHz

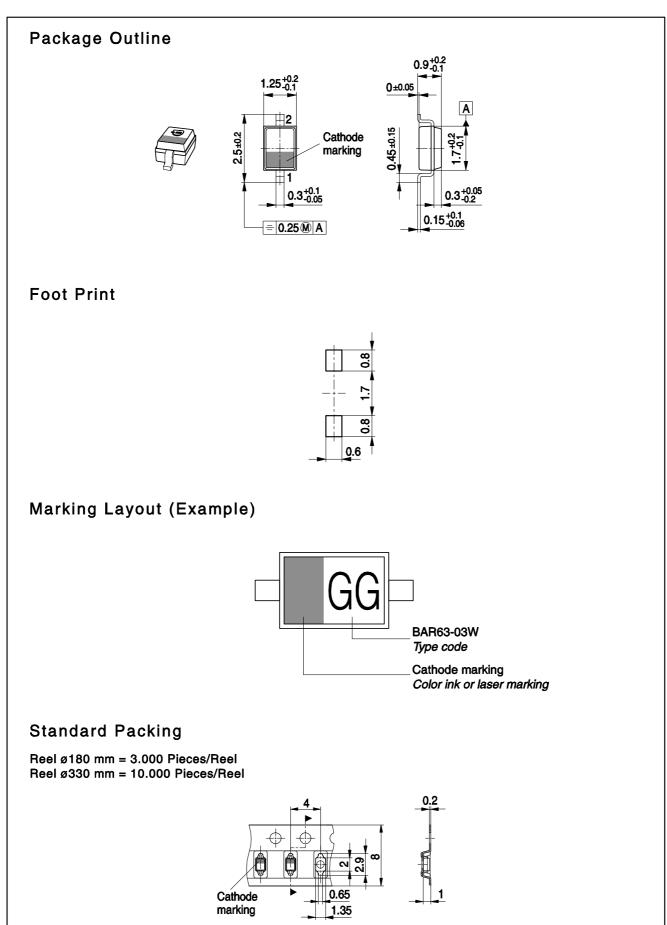


Temperature coefficient of the diode

capacitance  $T_{Cc} = f(V_R)$ 









Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

© 2009 Infineon Technologies AG All Rights Reserved.

#### Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

#### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (<<u>www.infineon.com</u>>).

#### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Infineon: BB439E6327HTSA1